

Tu2E-2

A 2.4-GHz MEMS-Based Oscillator with Phase Noise of -138 dBc/Hz at 100 kHz Offset and 226 dBc/Hz FoM

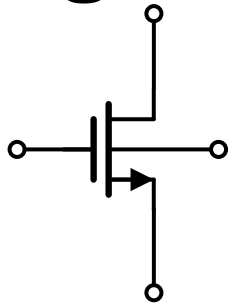
**Shiyue Ma, Keping Wang, Menglun Zhang,
and Kaixue Ma**

Tianjin University, Tianjin, China

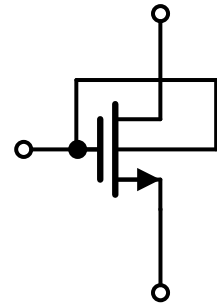
- **Motivation**
- **Proposed MEMS-Based Oscillator**
- **Circuit Implementation**
- **Experimental Results**
- **Conclusion**

- RF oscillators are one of essential modules
 - Small size, low phase noise, low power
- Micro-Electro-Mechanical-System (MEMS) oscillators are attractive
 - High Q-factor(> 1000)
 - ✓ Improve phase noise
 - ✗ A longer start-up time
 - Integration potential, low cost
- Shorten start-up time helps to save power

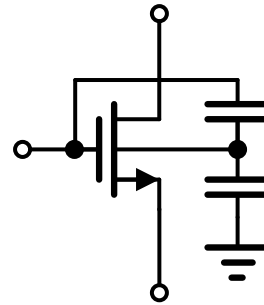
- G_m -boosting techniques are used to shorten start-up time and decrease power
 - Darlington cell
 - Body biasing
- Body biasing scheme



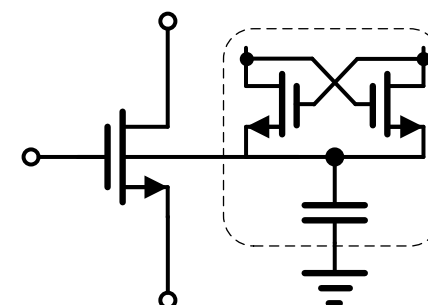
<Traditional>



<Gate-feedback[7]>

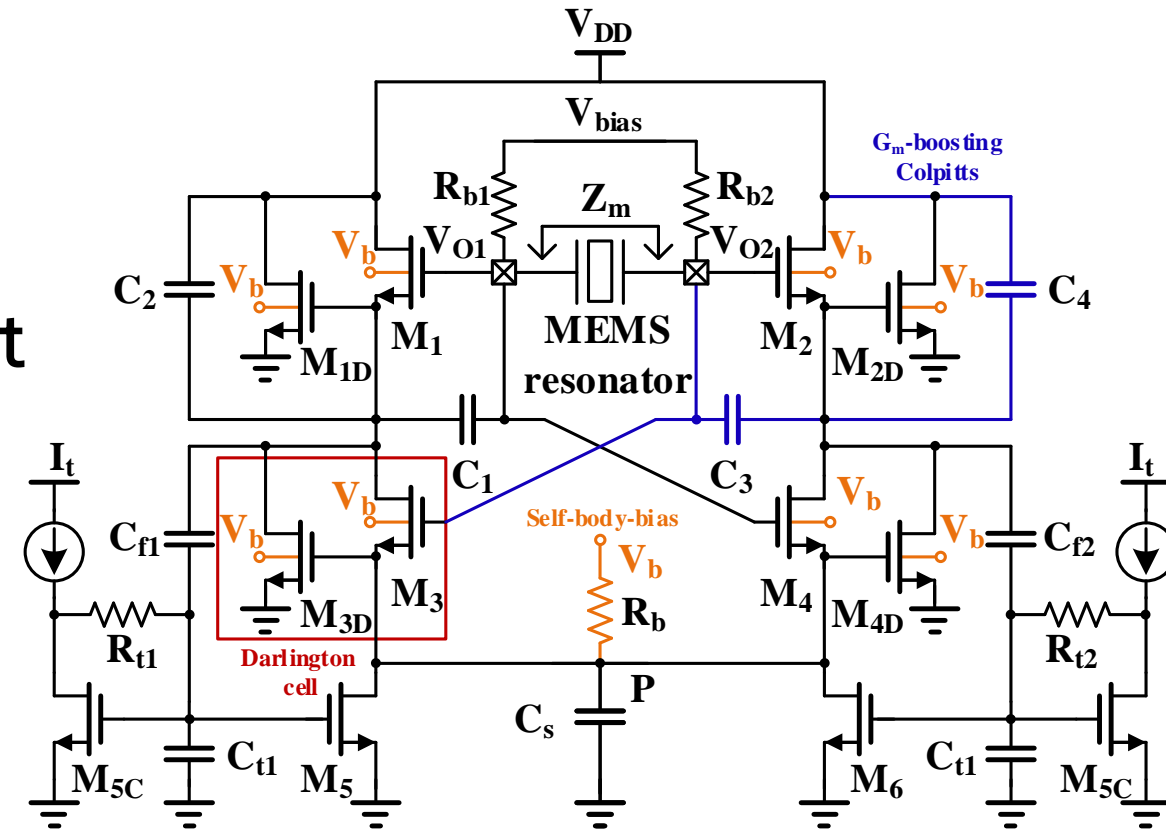


<Capacitive-division feedback[8]>

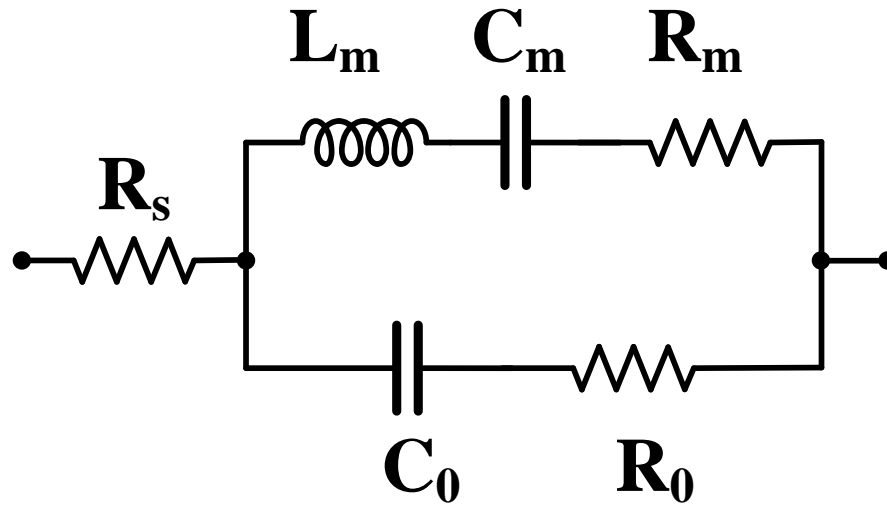


<Amplitude detector-added[10]>

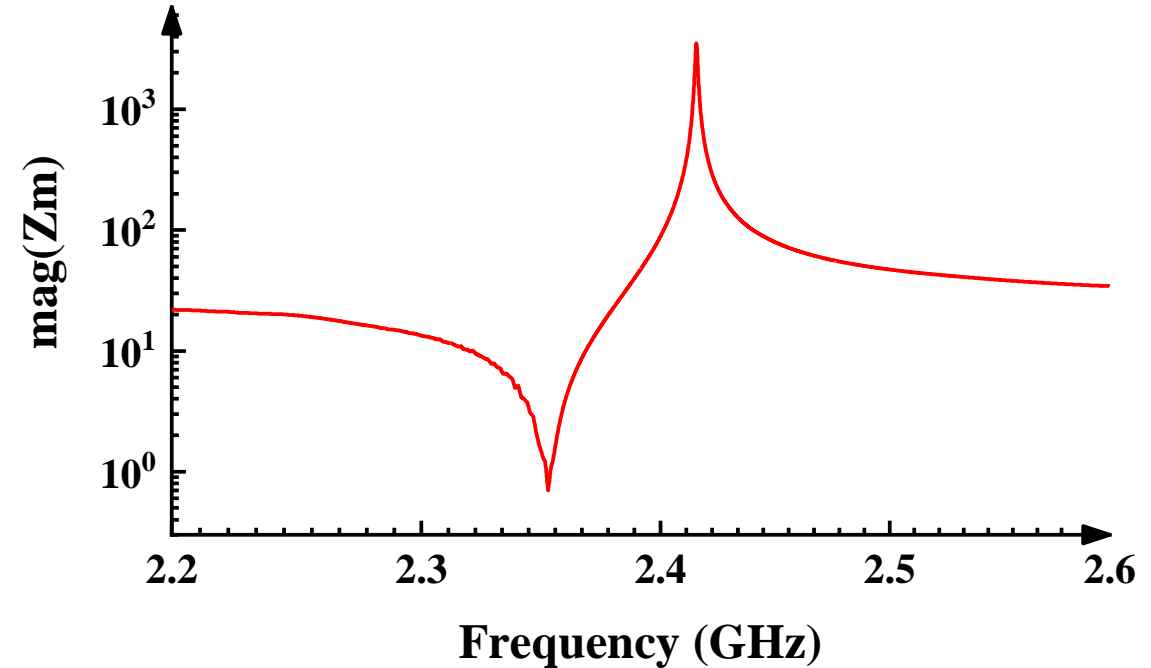
- G_m -boosting differential Colpitts
- Dynamic self-body-biasing scheme
- Benefits
 - Senses the voltage from internal circuit to bulk terminal
 - Limitation on output swing is relaxed
 - Deterioration of phase noise caused by large amplitude is decreased



- Off-chip MEMS resonator is used for high-Q tank

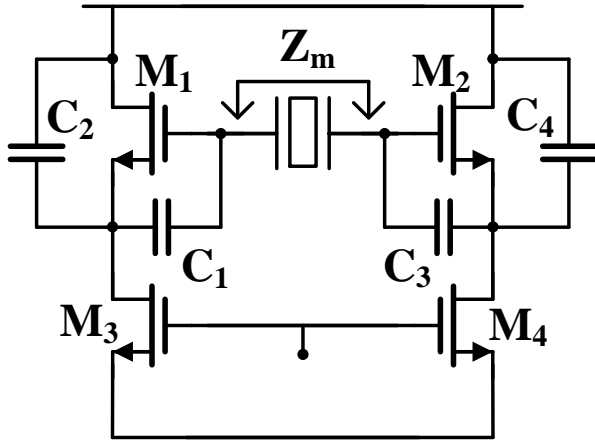


<MBVD model>

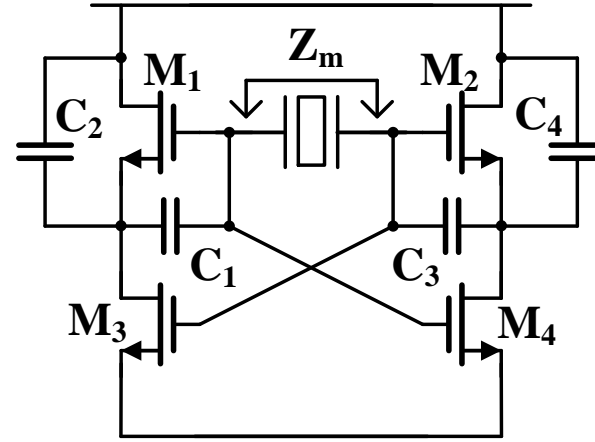


<Impedance response>

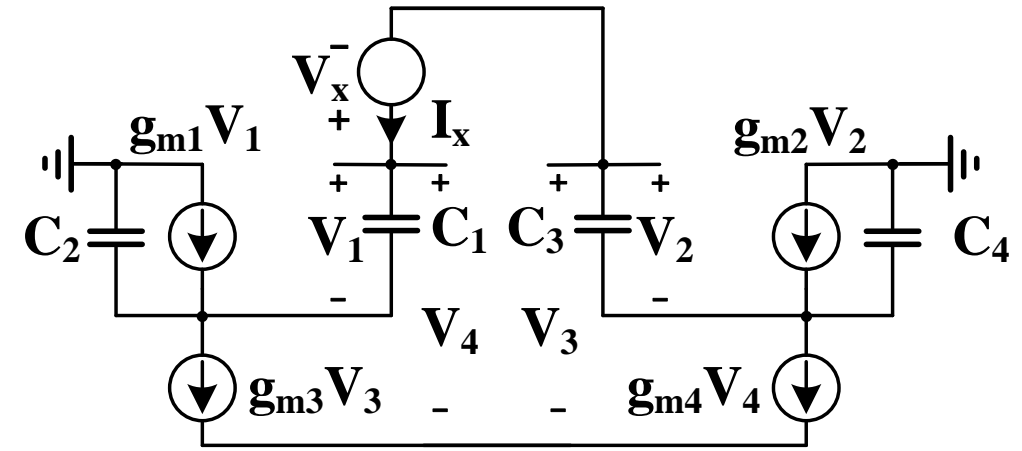
G_m -boosting differential Colpitts



<Conventional differential Colpitts>



<Gm-boosting Colpitts>



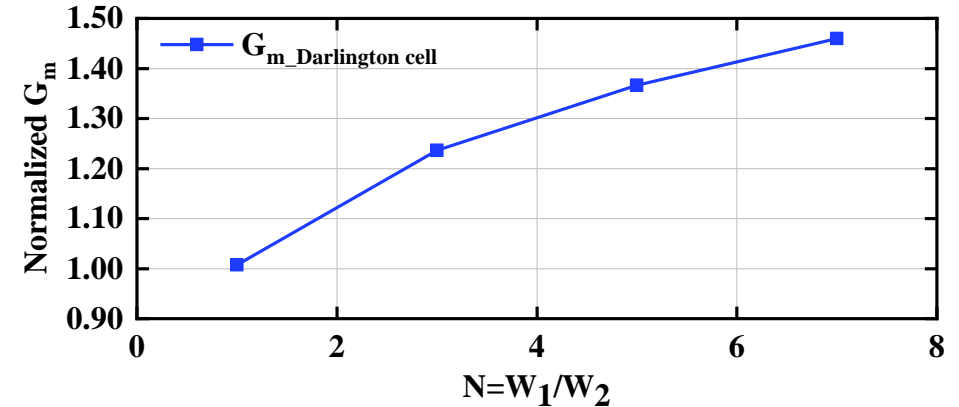
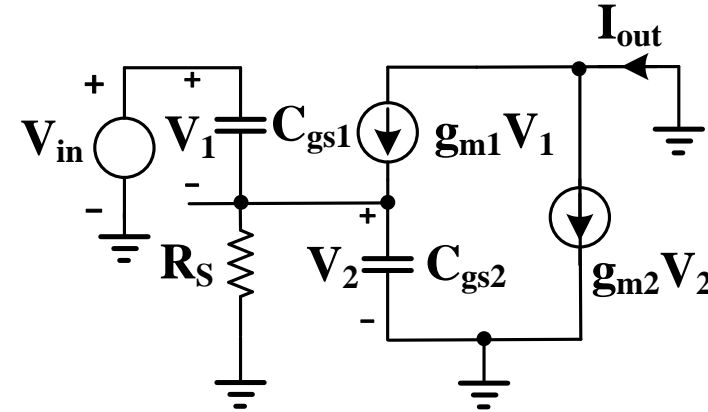
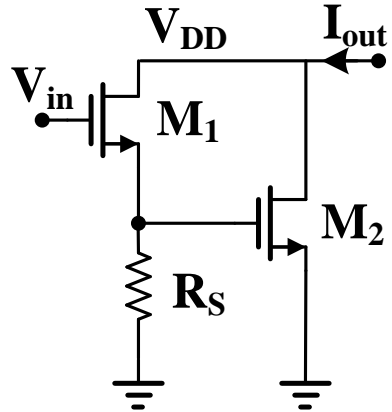
<Small signal model of gm-boosting Colpitts>

- Assuming that, $g_{m1}=g_{m2}$, $g_{m3}=g_{m4}$

$$\text{Re}G_m = -\frac{1}{2} \frac{\omega^2 C_1 C_2 g_{m1}}{g_{m1}^2 + \omega^2 (C_1 + C_2)^2} \left(1 + \frac{g_{m3}}{g_{m1}} \left(1 + \frac{C_1}{C_2} \right) \right)$$

G_m -boosting

Darlington cell



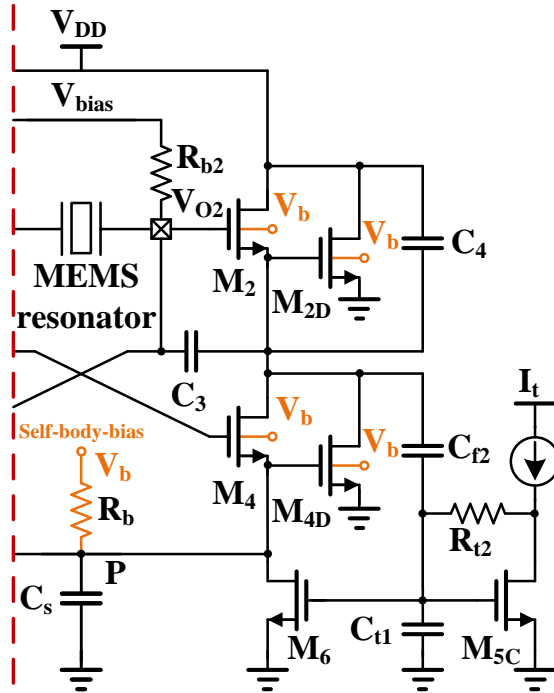
<Basic Darlington cell structure>

<Small signal equivalent circuit model of Darlington cell>

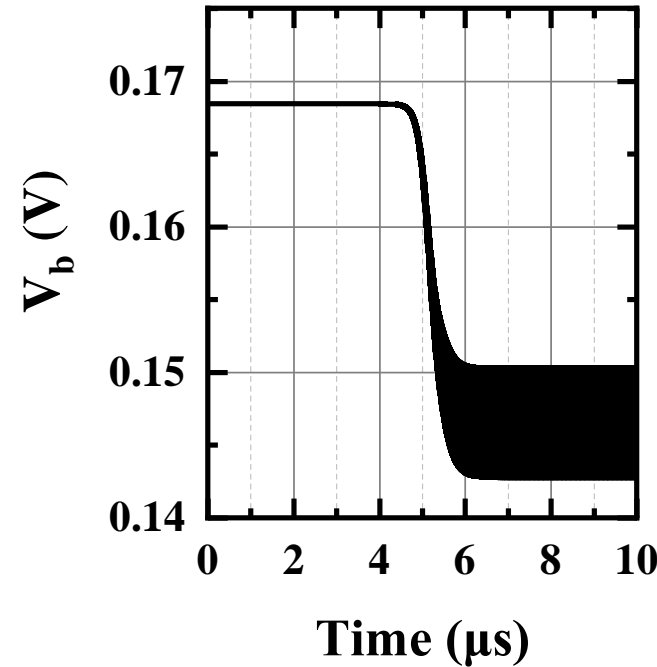
<Normalized transconductance of Darlington cell vary with N>

- $$G_m(D) = \frac{g_{m1}(1 + g_{m2}R_S) + (g_{m1}C_{gs2} + g_{m2}C_{gs1})sR_S}{1 + g_{m1}R_S + (C_{gs1} + C_{gs2})sR_S}$$
- $G_m(D)$ would be **optimized by properly selecting the size of M_1 and M_2**
- N is the size ratio of M_1 and M_2 . Here, **$N=5$**

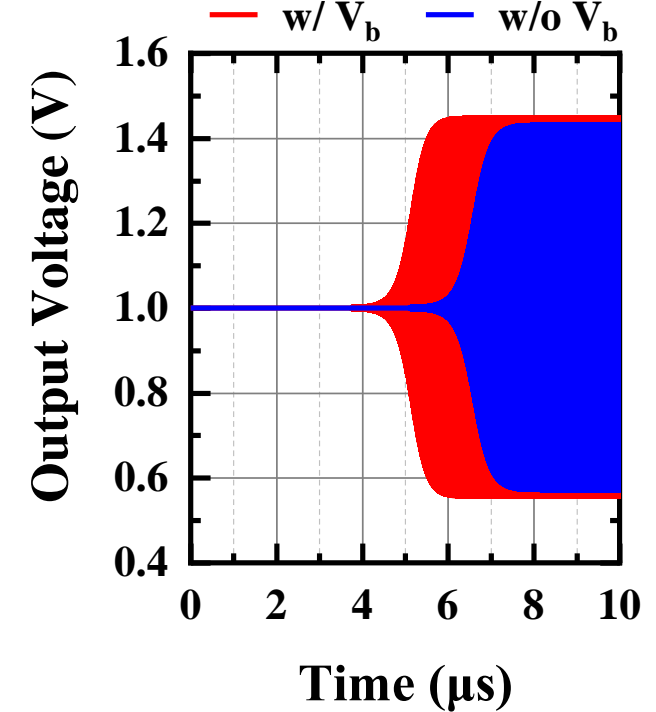
Self-body-biasing



<self-body-biasing>



<Simulation of body bias V_b >

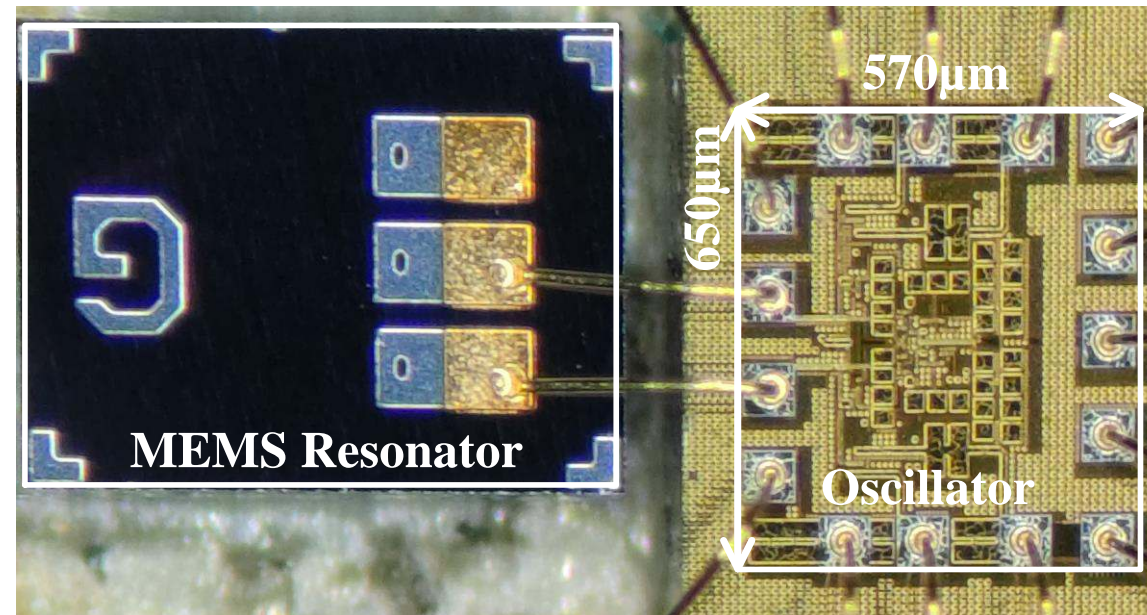


<Simulation of output swing V_{O1} >

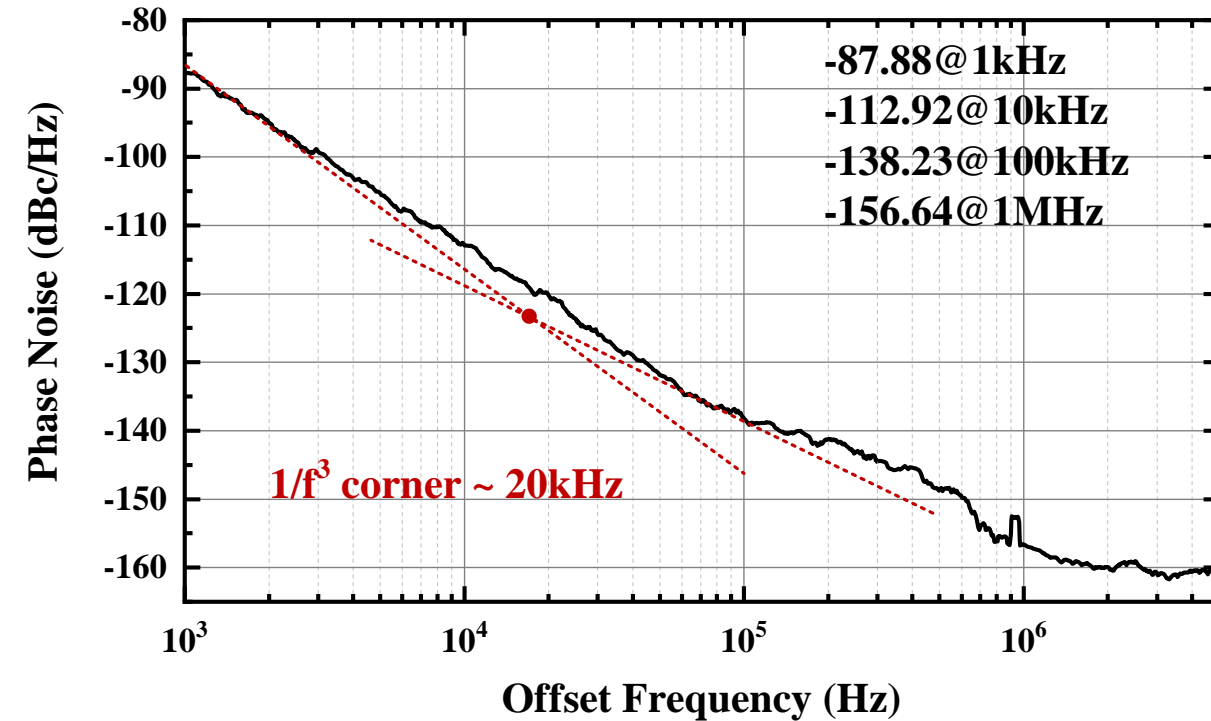
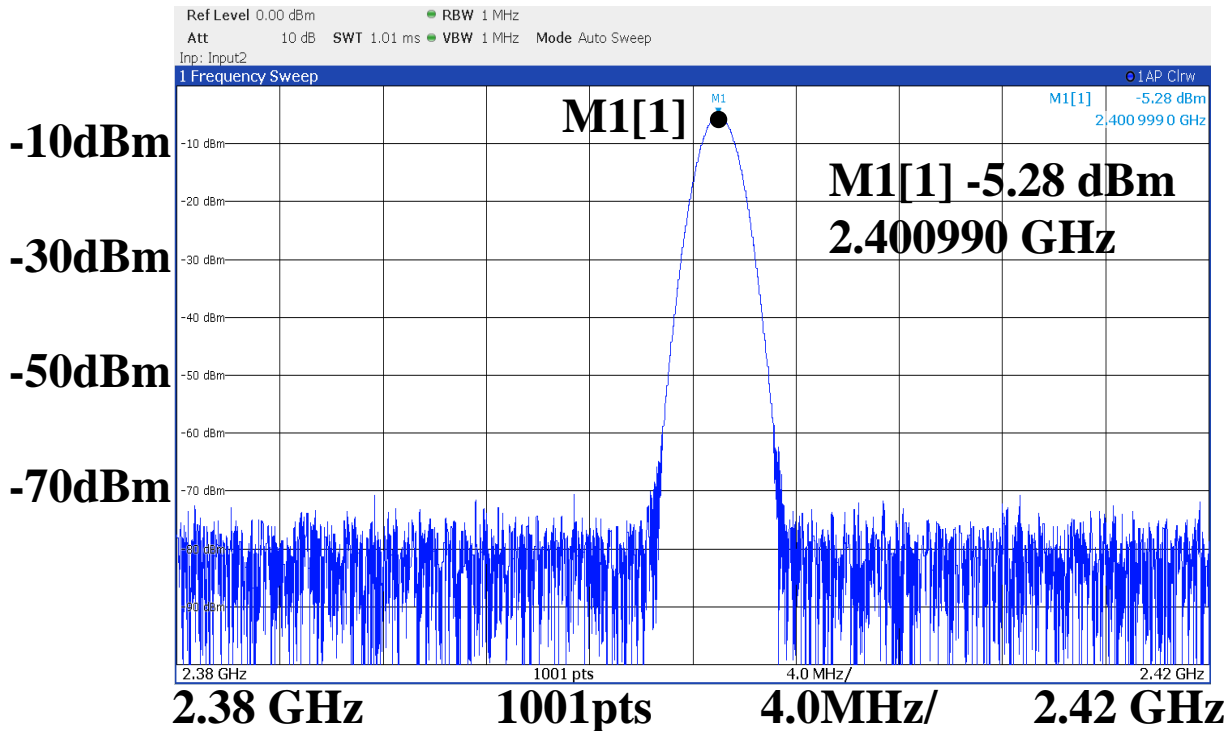
- Dynamic self-body-biasing improves the start-up safety
- Start-up time can be further shorten by adding V_b (red curve) based on the g_m -boosting Colpitts using Darlington cell (blue curve)

Chip Micrograph

- Fabricated with 180-nm CMOS
- The area of the CMOS chip is $650\text{ }\mu\text{m} \times 570\text{ }\mu\text{m}$ including pads

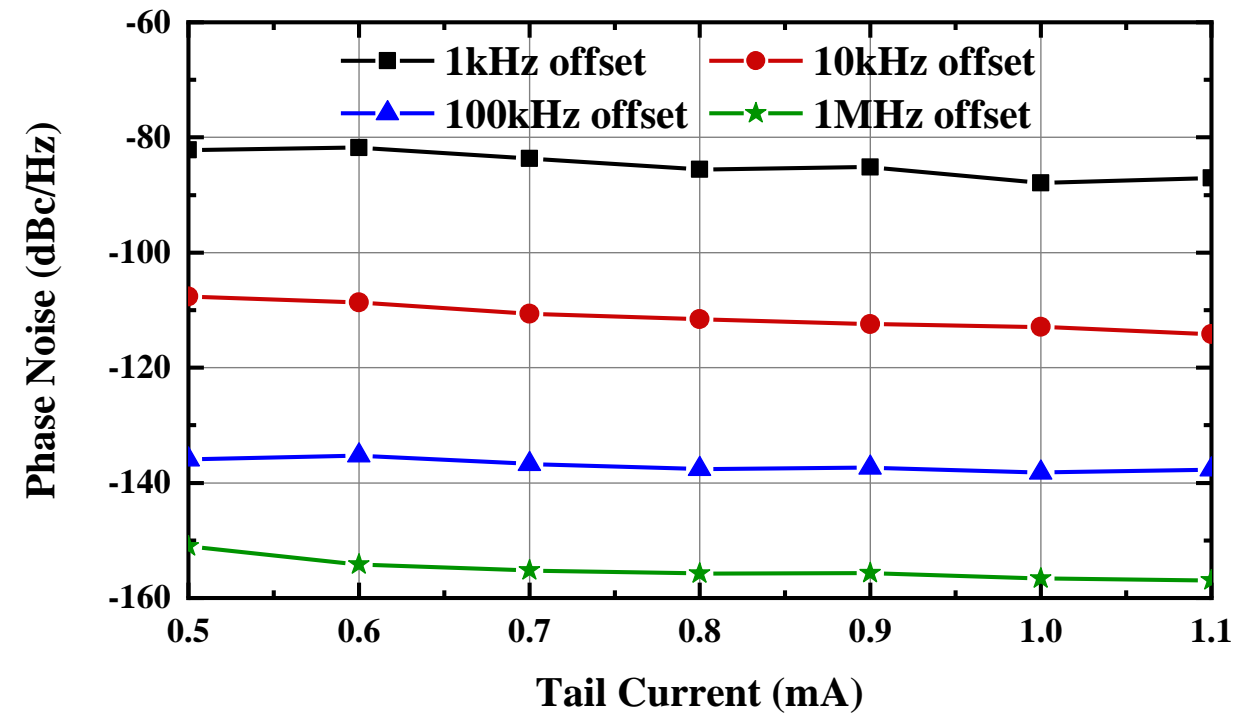
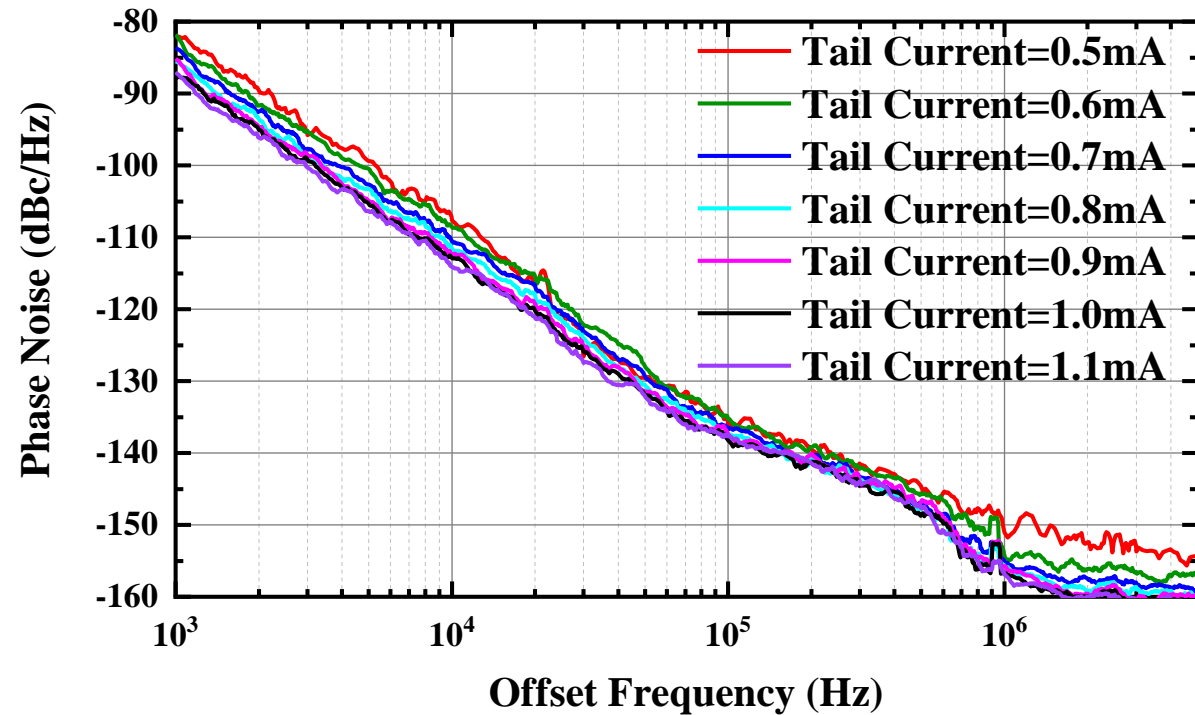


Measured phase noise



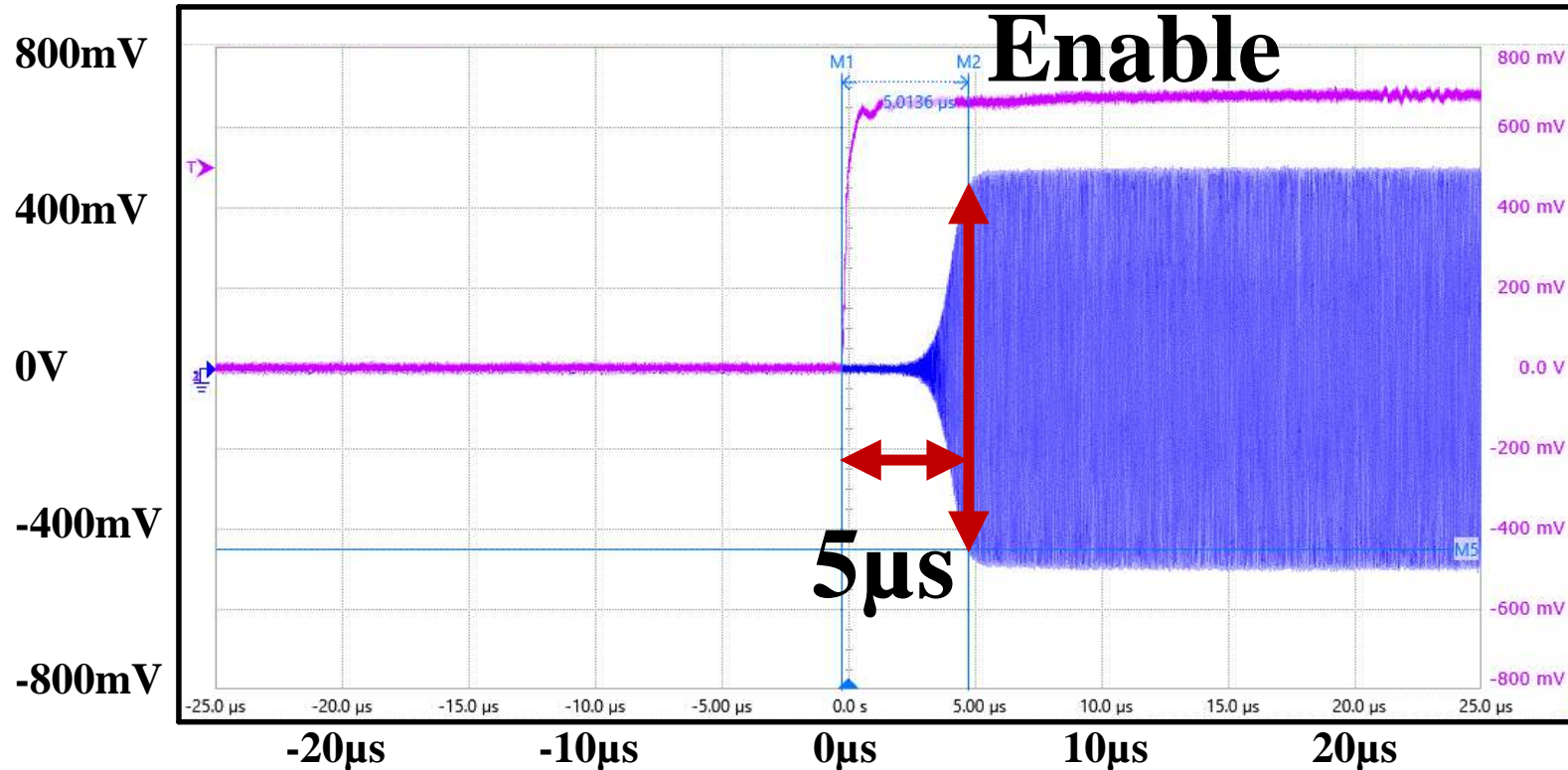
- P_{DC} : 0.98 mW @ 0.7 V supply
- P_{out} : -5.28 dBm at 2.4 GHz
- Phase noise: -138.23 dBc/Hz@100kHz; -156.64 dBc/Hz@1MHz

Measured phase noise



- Measured phase noise across tail current from 0.5 to 1.1 mA
- Measured phase noise performance is quite stable

Measured start-up time



- Measured using KEYSIGHT DSOS404A Digital Storage Oscilloscope
- It stabilizes within $\sim 5 \mu\text{s}$

Performance comparison

Reference	Techn. (nm)	Freq. (GHz)	VDD (V)	PN@1kHz (dBc/Hz)	PN@10kHz (dBc/Hz)	PN@100kHz (dBc/Hz)	PN@1MHz (dBc/Hz)	Start-up time (μs)	PDC (mW)	FoM (dBc/Hz)
[3]CICC'11	130	2	0.6	-68*	-102*	-128	-149	N/A	0.126	224
[11]RFIC'13	130	1.925	1.2	-88.3	-116	-137.2	-146	N/A	1.6	220
[12]EuMIC'14	180	1.984	1.1	-73.23	-100.74	-124.85	-148	N/A	1.7	212
[13]ISSCC'15	65	0.75	0.75	-90*	-115*	-135*	-145	N/A	0.45	216**
[14]TCAS-2'19	65	2	0.6	-68.6	-96.4	-127	-141	N/A	0.35	217
[15]RFIC'21	7	2.492	0.8	-77*	-104*	-128	-140*	N/A	0.416	220
[16]TMTT'15	65	2.46-2.5	1.2	-65*	-96*	-121	-130*	2	1.32	207**
[17]VLSI'19	65	2.4	1.5	-70*	-100*	-120	-127*	<10	>1**	N/A
This work	180	2.4	0.7	-87.88	-112.92	-138.23	-156.64	5	0.98	226

* Extracted from measurement plot ** Calculated
$$\text{FoM} = 20 \log \left(\frac{f_0}{\Delta f} \right) - 10 \log \left(\frac{P_{\text{DC}}}{1 \text{ mW}} \right) - L(\square f)$$

- A 2.4-GHz MEMS-based oscillator with g_m -boosting technique was designed
- A novel Darlington cell with a dynamic self-body-biasing scheme was proposed
- It has the features of
 - Short start-up time
 - Low phase noise
 - Excellent FoM

Thank you!